

29. (New) The transistor of claim 25, wherein said lower portion of said gate electrode is comprised of polysilicon.

30. (New) The transistor of claim 25, wherein said upper portion of said gate electrode is comprised of polysilicon.

31. (New) The transistor of claim 25, wherein said extensions are comprised of polysilicon.

32. (New) The transistor of claim 25, wherein said upper portion of said gate electrode and said extensions have a combined lateral dimension that is approximately 5-100 percent greater than a lateral dimension of said lower portion of said gate electrode.

#### REMARKS

It is believed that a fee in the amount of \$144.00 is required in connection with this amendment. **The Assistant Commissioner is authorized to deduct any fees required under 37 C.F.R. §§ 1.16 to 1.21 from the Advanced Micro Devices, Inc. Deposit Account No. 01-0365/DE0053.** In the event the monies in that account are insufficient, the Assistant Commissioner is authorized to withdraw funds from Williams, Morgan & Amerson, P.C. Deposit Account No. 50-0786/2000.064200.

The Examiner is invited to contact the undersigned attorney at (713) 934-4055 with any questions, comments or suggestions relating to the referenced patent application.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'J. Mike Amerson', written over a horizontal line.

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